

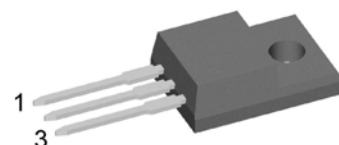
HiPerFRED²

$$\begin{aligned} V_{RRM} &= 300\text{ V} \\ I_{FAV} &= 2 \times 10\text{ A} \\ t_{rr} &= 35\text{ ns} \end{aligned}$$

High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Common Cathode

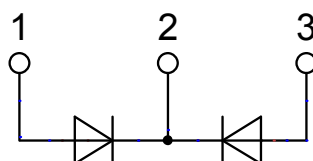
Part number

DPG20C300PN



Backside: isolated

 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

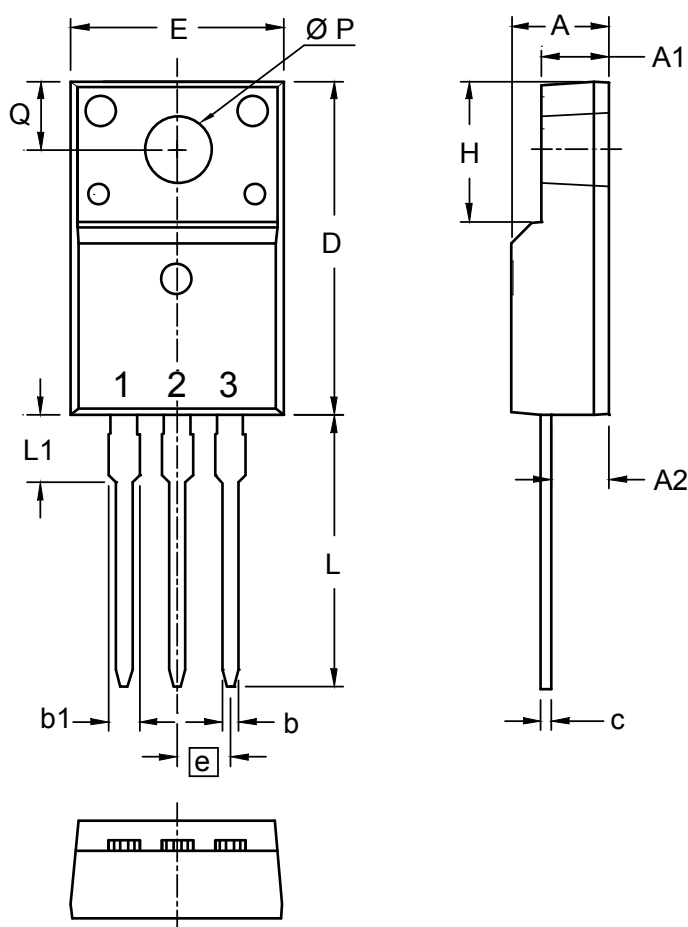
Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Base plate: Plastic overmolded tab
- Reduced weight

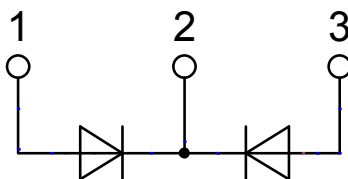
Fast Diode				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				300	V
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}\text{C}$				300	V
I_R	reverse current, drain current	$V_R = 300\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$			1	μA
		$V_R = 300\text{ V}$	$T_{VJ} = 150^{\circ}\text{C}$			0.06	mA
V_F	forward voltage drop	$I_F = 10\text{ A}$	$T_{VJ} = 25^{\circ}\text{C}$			1.27	V
		$I_F = 20\text{ A}$				1.45	V
		$I_F = 10\text{ A}$	$T_{VJ} = 150^{\circ}\text{C}$			0.98	V
		$I_F = 20\text{ A}$				1.17	V
I_{FAV}	average forward current	$T_C = 125^{\circ}\text{C}$ rectangular $d = 0.5$	$T_{VJ} = 175^{\circ}\text{C}$			10	A
V_{FO}	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^{\circ}\text{C}$		0.74	V
r_F	slope resistance					17.7	m Ω
R_{thJC}	thermal resistance junction to case					4.4	K/W
R_{thCH}	thermal resistance case to heatsink				0.50		K/W
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$				35	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$	$T_{VJ} = 45^{\circ}\text{C}$			140	A
C_J	junction capacitance	$V_R = 150\text{ V}$ $f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}\text{C}$		15		pF
I_{RM}	max. reverse recovery current	$I_F = 10\text{ A}; V_R = 200\text{ V}$ -di _F /dt = 200 A/ μs		$T_{VJ} = 25^{\circ}\text{C}$		3	A
				$T_{VJ} = 125^{\circ}\text{C}$		5.5	A
				$T_{VJ} = 25^{\circ}\text{C}$		35	ns
				$T_{VJ} = 125^{\circ}\text{C}$		45	ns
t_{rr}	reverse recovery time						

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Outlines TO-220FP



Dim.	Millimeters		Inches	
	min	max	min	max
A	4.50	4.90	0.177	0.193
A1	2.34	2.74	0.092	0.108
A2	2.56	2.96	0.101	0.117
b	0.70	0.90	0.028	0.035
c	0.45	0.60	0.018	0.024
D	15.67	16.07	0.617	0.633
E	9.96	10.36	0.392	0.408
e	2.54 BSC		0.100 BSC	
H	6.48	6.88	0.255	0.271
L	12.68	13.28	0.499	0.523
L1	3.03	3.43	0.119	0.135
Ø P	3.08	3.28	0.121	0.129
Q	3.20	3.40	0.126	0.134



Fast Diode

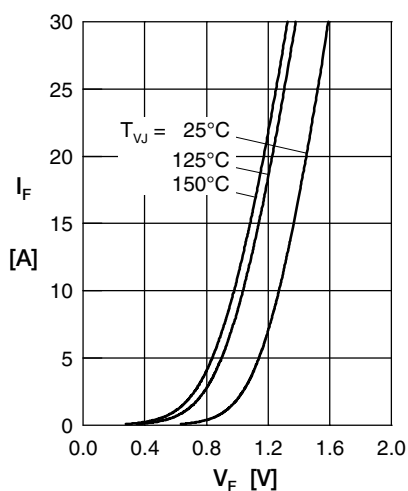


Fig. 1 Forward current
 I_F versus V_F

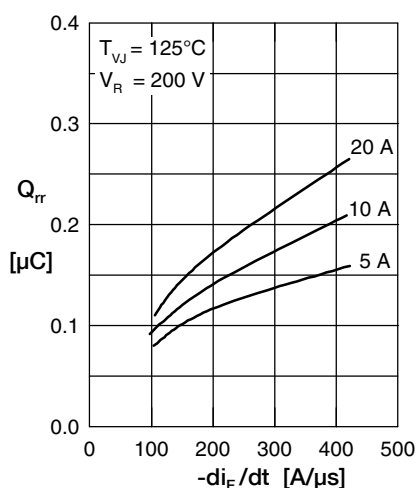


Fig. 2 Typ. reverse recov. charge
 Q_{rr} versus $-di_F/dt$

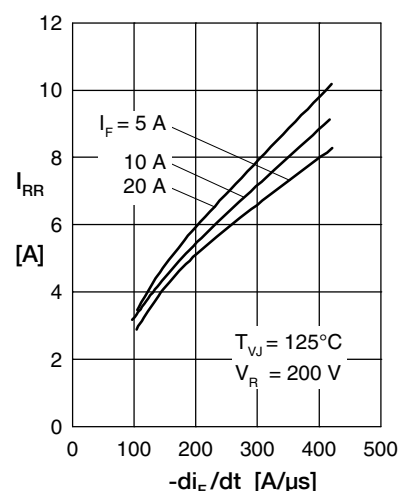


Fig. 3 Typ. reverse recov. current
 I_{RR} versus $-di_F/dt$

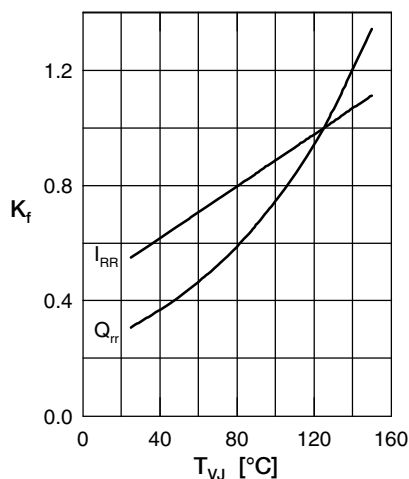


Fig. 4 Typ. dynamic parameters
 Q_{rr} , I_{RR} versus T_{VJ}

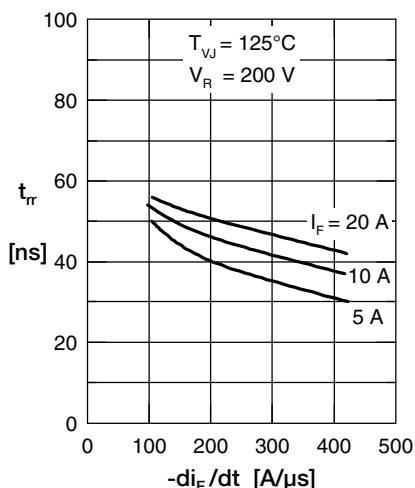


Fig. 5 Typ. reverse recov. time
 t_{rr} versus $-di_F/dt$

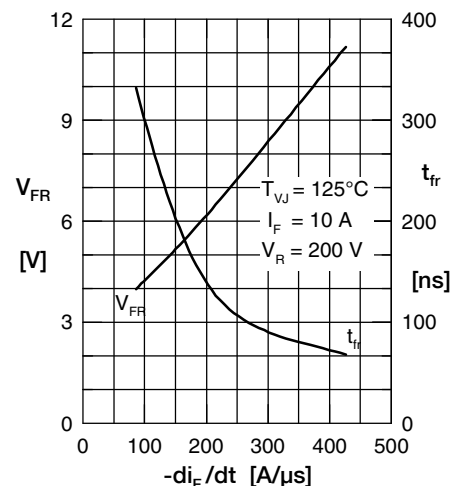


Fig. 6 Typ. forward recov. voltage
 V_{FR} and t_{fr} versus $-di_F/dt$

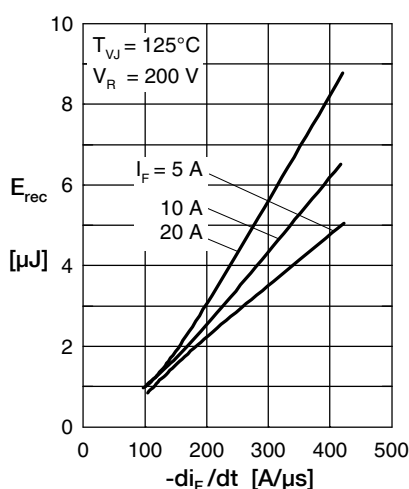


Fig. 7 Typ. recovery energy
 E_{rec} versus $-di_F/dt$

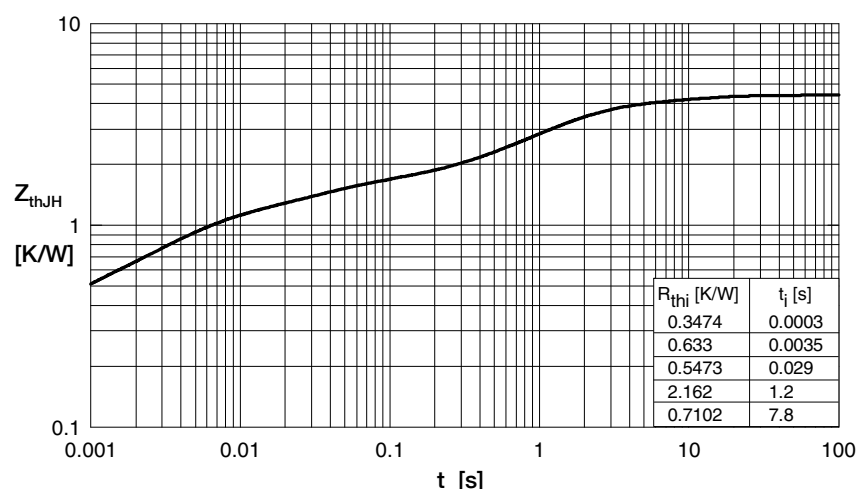


Fig. 8 Transient thermal resistance junction to case